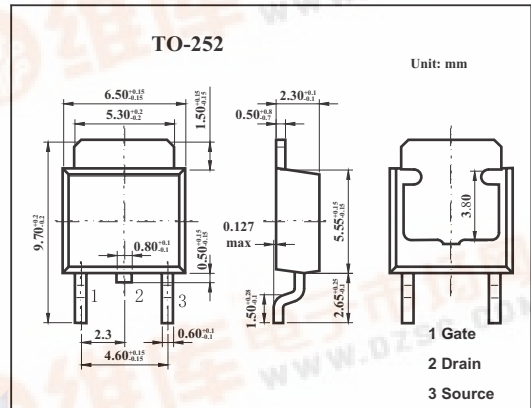
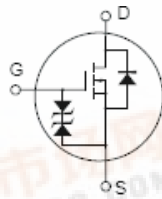


SMD Type MOSFET

Silicon N-Channel MOSFET  
2SK1880S

Features

- Low on-resistance
- High speed switching
- No secondary breakdown
- Suitable for Switching regulator



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V <sub>DSS</sub>	600	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	1.5	A
Power dissipation	P <sub>D</sub>	20	W
Channel temperature	T <sub>ch</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain source breakdown voltage	V <sub>DSS</sub>	I <sub>D</sub> =10mA, V <sub>GS</sub> =0	600			V
Gate to source breakdown voltage	V <sub>GSS</sub>	I <sub>D</sub> =±100 μA, V <sub>DS</sub> =0	±30			V
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> =500V, V <sub>GS</sub> =0			100	μA
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±25V, V <sub>DS</sub> =0			±10	μA
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =1A	0.85	1.4		S
Drain to source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =1A		6.5	8.0	Ω
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0, f=1MHZ		250		pF
Output capacitance	C <sub>oss</sub>				55	pF
Reverse transfer capacitance	C <sub>rss</sub>				8	pF
Turn-on delay time	t <sub>d(on)</sub>	I <sub>D</sub> =1A, V <sub>GS(on)</sub> =10V, R <sub>L</sub> =30 Ω		10		ns
Rise time	t <sub>r</sub>				25	ns
Turn-off delay time	t <sub>d(off)</sub>				35	ns
Fall time	t <sub>f</sub>				30	ns

